

**FOR IMMEDIATE RELEASE**  
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**Online resource answers questions about using and evaluating GaN technology...**

## **NITRONEX LAUNCHES GAN ESSENTIALS™ INITIATIVE TO EDUCATE THE INDUSTRY REGARDING GAN-ON-SI TECHNOLOGY**

**ATLANTA, International Microwave Symposium, booth 2108, (June 16, 2008) —** Building on its position as the leading producer of gallium nitride on silicon (GaN-on-Si) RF devices, Nitronex has launched an initiative to educate the industry regarding the use of this unique technology. Nitronex's new GaN Essentials™ education center provides visitors with a better understanding of how to evaluate performance of, and design with, GaN in RF power applications.

“As the leading worldwide GaN-on-Si supplier, our engineering, marketing and sales teams receive many inquiries concerning our GaN technology. We took the most common questions and developed a set of application notes that answer them,” said Ray Crampton, Nitronex Director of Marketing. “Evaluating and designing with a new technology can raise new questions and pose new challenges. The GaN Essentials collection is part of our efforts to make designing with GaN as easy as possible. We will continue to develop application notes and update the GaN Essentials education center to address the industry's questions.”

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The GaN Essentials education center is available at [www.nitronex.com/ganessentials.html](http://www.nitronex.com/ganessentials.html) and initially discusses the following topics:

- Comparison of LDMOS and GaN for RF power amplifiers and basic concepts and approximations used for LDMOS with the equivalent information for GaN products
- Comparisons of substrates used for GaN RF devices since the choice of substrate affects affordability, availability, reliability and performance
- Thermal design data and simulations for GaN technology in plastic and ceramic air cavity packages
- Proper biasing, sequencing, and temperature compensation of GaN HEMTs
- Broadband design, methodology and performance of RF power amplifiers utilizing GaN technology

For more information about Nitronex's GaN Essentials education center or GaN-on-Si products, contact Nitronex at 2305 Presidential Dr., Durham, NC, 27703; call 919-424-9100; e-mail [info@nitronex.com](mailto:info@nitronex.com); or visit [www.nitronex.com](http://www.nitronex.com).

### **About Nitronex**

Specializing in the development and manufacturing of gallium nitride-on-silicon (GaN-on-Si) RF power devices, Nitronex is the global leader in high-performance GaN-on-Si RF power devices. Based on its patented SIGANTIC® process – gallium nitride on silicon technology – Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 19 patents with 19 others pending.

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